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U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Fees pursuant to the Consolidated Appropriations Act, 2005 (H.R. 4818).

FEE TRANSMITTAL

For FY 2006

Complete if Known

09/4215 18

<input type="checkbox"/> Applicant claims small entity status. See 37 CFR 1.27	Application Number	Patent#: 6,951,805
	Filing Date	Issued: October 4, 2005
	First Named Inventor	John T. Moore
	Examiner Name	P. T. Dang
	Art Unit	2818
	Attorney Docket No.	M4065.0696/P696
TOTAL AMOUNT OF PAYMENT	(\$)	100.00

METHOD OF PAYMENT (check all that apply)

☐ Check ☒ Credit Card ☐ Money Order ☐ None ☐ Other (please identify): _____

☐ Deposit Account Deposit Account Number: 04-1073 Deposit Account Name: Dickstein Shapiro Morin & Oshinsky LLP

For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)

☒ Charge fee(s) indicated below ☐ Charge fee(s) indicated below, except for the filing fee

☐ Charge any additional fee(s) or underpayment of fee(s) under 37 CFR 1.16 and 1.17 ☒ Credit any overpayments

FEE CALCULATION (All the fees below are due upon filing or may be subject to a surcharge.)

1. BASIC FILING, SEARCH, AND EXAMINATION FEES

Application Type	FILING FEES		SEARCH FEES		EXAMINATION FEES		Fees Paid (\$)
	Fee (\$)	Small Entity Fee (\$)	Fee (\$)	Small Entity Fee (\$)	Fee (\$)	Small Entity Fee (\$)	
Utility	300	150	500	250	200	100	
Design	200	100	100	50	130	65	
Plant	200	100	300	150	160	80	
Reissue	300	150	500	250	600	300	
Provisional	200	100	0	0	0	0	

2. EXCESS CLAIM FEES

Fee Description	Fee (\$)	Small Entity Fee (\$)
Each claim over 20 (including Reissues)	50	25
Each independent claim over 3 (including Reissues)	200	100
Multiple dependent claims	360	180

<u>Total Claims</u>	<u>Extra Claims</u>	<u>Fee (\$)</u>	<u>Fee Paid (\$)</u>	<u>Multiple Dependent Claims</u>	<u>Fee (\$)</u>	<u>Fee Paid (\$)</u>
HP = highest number of total claims paid for, if greater than 20.						
<u>Indep. Claims</u>	<u>Extra Claims</u>	<u>Fee (\$)</u>	<u>Fee Paid (\$)</u>			
HP = highest number of independent claims paid for, if greater than 3.						

3. APPLICATION SIZE FEE

If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).

Total Sheets	Extra Sheets	Number of each additional 50 or fraction thereof	Fee (\$)	Fee Paid (\$)
- 100 =	/50	(round up to a whole number) x	=	

4. OTHER FEE(S)

Non-English Specification, \$130 fee (no small entity discount)	
Other (e.g., late filing surcharge): 1811 Certificate of correction	100.00
	Fees Paid (\$)

SUBMITTED BY			
Signature		Registration No. (Attorney/Agent)	28,371
Name (Print/Type)	Thomas J. D'Amico	Telephone	(202) 828-2232
		Date	Dec 28, 2006

of Correction
JUL 03 2006



Docket No.: M4065.0696/P696
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
John T. Moore

Patent No.: 6,951,805

Issued: October 4, 2005

For: METHOD OF FORMING INTEGRATED
CIRCUITRY, METHOD OF FORMING
MEMORY CIRCUITRY, AND METHOD OF
FORMING RANDOM ACCESS MEMORY
CIRCUITRY (AMENDED)

**REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 CFR 1.322 & 1.323**

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted typographical errors which should be corrected.

In the Specification, the PTO made the following error to be corrected:

Column 3, line 56, "spacers 29" should read --spacers 30--.

In the Other Publications portion of the References Cited section the PTO made the following errors to be corrected:

06/29/2006 SZEWDIE1 00000126 6951805

01 FC:1811

100.00 OP

"Alekperova, Sh.M.; Gadshleva, G.S., Current-Voltage characteristics of Ag₂Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139."

Should read

--Alekperova, Sh.M.; Gadzhieva, G.S., Current-voltage characteristics of Ag₂Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.--;

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"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985."

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"Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally Induced crystallization of amorphous $\text{Ge}_{0.4}\text{Se}_{0.6}$, J. Non-Cryst. Solids 117-118 (1990) 219-221."

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"Yoji Kawamoto et al., "Ionic Conduction in $\text{As}_2\text{S}_3\text{-Ag}_2\text{S}_1\text{GeSe}_2\text{-GeS}_2\text{-Ag}_2\text{S}$ and $\text{P}_2\text{S}_5\text{-Ag}_2\text{S}$ Glasses," Journal of Non-Crystalline Solids 20 (1976) 393-404."

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Also in the Other Publications portion of the References Cited section, Applicant made the following error to be corrected:

"Miyatani, *Electrical Porperties of Ag_2Se* , 13 J. Phys. Soc. Japan, p. 317 (1958)."

Should read

--Miyatani, *Electrical Properties of Ag_2Se* , 13 J. Phys. Soc. Japan, p. 317 (1958).--.

The errors were both found in the application as filed by Applicants and made by the PTO. Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed.

The errors now sought to be corrected are inadvertent typographical errors the correction of which does not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentee respectfully solicits the granting of the requested Certificate of Correction.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0696/P696.

Dated: June 28, 2006

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

Megan S. Woodworth

Registration No.: 53,655

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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 3

PATENT NO. : 6,951,805
APPLICATION NO. : 09/921,518
ISSUE DATE : October 4, 2005
INVENTOR : John T. Moore

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Specification, the following error is corrected:

Column 3, line 56, "spacers 29" should read --spacers 30--.

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MAILING ADDRESS OF SENDER (Please do not use customer number below):

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Should read

--Gates, B.; Wu, Y.; Yin, Y.; Yang, P.; Xia, Y., Single-crystalline nanowires of Ag_2Se can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP.--;

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2101 L Street NW
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2003

--West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the $\text{Ag}|\text{As}_{0.24}\text{S}_{0.36}\text{Ag}_{0.40}|\text{Ag}$ System prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974.--;

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